

This application is a Continuation application of U.S. Application No. 10/424,105, filed April 28, 2003, <sup>now Patent No. 6,855,642</sup> which is a Continuation application of U.S. Serial No. 09/939,600, filed August 28, 2001, now U.S. Patent No. 6,596,650, issued July 22, 2003, which is a Continuation application of U.S. Serial No. 09/494,036, filed January 31, 2000, now U.S. Patent No. 6,518,201, issued February 11, 2003, which is a Continuation application of U.S. Serial No. 09/380,646, filed September 7, 1999, now U.S. Patent No. 6,239,041, issued May 29, 2001, which is an application filed under 35 USC 371 of PCT/JP98/00892, filed March 4, 1998. The contents of No. 09/380,646 are incorporated herein by reference in their entirety.

#### Technical Field

This invention relates to a method for fabricating semiconductor integrated circuit devices including semiconductor devices, and more particularly, to a technique useful for application to the formation of gate oxide films (insulating films) such as of MOSFET (metal oxide semiconductor field effect transistor)

#### Background Art

In the initial stage of semiconductor industries, bubbling was in wide use where a carrier gas such as oxygen or the like was passed through water in a bubbler. Although this technique was advantageous in that a wide range of a moisture content could be covered, a problem on pollution could not be avoided, and thus, the technique is rarely used at present. Accordingly, an oxygen and hydrogen combustion method, i.e. a pyrogenic system, has been widespread in order to avoid the disadvantage of the bubbler.

(Disclosure of Prior Art Literature, etc.)

With regard to an improvement in thermal oxidation and a moisture generation method thereto, to which the invention is directed, the following prior art techniques

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illustrating a method for fabricating a semiconductor integrated circuit device according to embodiment 1 of the invention.

Fig. 7 is a sectional view of an essential part illustrating a method for fabricating a semiconductor integrated circuit device according to embodiment 1 of the invention.

Fig. 8 is a sectional view of an essential part illustrating a method for fabricating a semiconductor integrated circuit device according to embodiment 1 of the invention.

Fig. 9 is a schematic view showing an oxide film forming apparatus of the single wafer type used to form a gate oxide film.

Fig. 10 is a sectional view of an essential part illustrating a method for fabricating a semiconductor integrated circuit device according to embodiment 1 of the invention.

Fig. 11(a) is a schematic plan view showing an example of an arrangement of an oxide film forming chamber, and (b) is a sectional view taken along line B-B' of (a).

Fig. 12(a) is a schematic plan view showing other example an arrangement of an oxide film forming chamber, and (b) is a sectional view taken along line B-B' of (a).

Fig. 13 is a schematic view showing a moisture generator of a catalyst type connected to an oxide film